

CLAIMS

What is claimed is:

1. A semiconductor workpiece, comprising
a metal layer;
5 an inorganic dielectric ARC layer disposed on the metal layer; and
a photoresist layer disposed on the ARC layer opposite the metal layer.

2. The workpiece recited in claim 1 wherein the ARC layer comprises silicon
oxynitride.

3. The workpiece recited in claim 2 wherein the ARC layer consists
essentially of silicon oxynitride.

4. The workpiece recited in claim 1 wherein the ARC layer has a
15 substantially uniform thickness over topical non-planarities on the metal layer.

5. The workpiece recited in claim 4 wherein the ARC layer is deposited on
the metal layer by chemical vapor deposition.

- 20 6. The workpiece recited in claim 5, wherein the ARC layer is deposited on
the metal layer by plasma enhanced chemical vapor deposition.

7. The workpiece recited in claim 1 wherein the photoresist layer is between
0.1 to 2 microns thick.

- 25 8. The workpiece recited in claim 7 where in the photoresist layer is 0.6 to
1.0 microns thick.

9. A metallic stack for a semiconductor interconnect, comprising:
a metal layer;
an inorganic dielectric ARC layer disposed on the metal layer; and
a barrier layer disposed on the metal layer opposite the arc layer.

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10. The metallic stack recited in claim 9 wherein the ARC layer comprises
silicon oxynitride.

11. The metallic stack recited in claim 10 wherein the ARC layer consists
10 essentially of silicon oxynitride.

12. The metallic stack recited in claim 9 wherein the ARC layer has a
substantially uniform thickness over topical non-planarities on the metal layer.

15 13. The metallic stack recited in claim 12 the ARC layer is deposited on the
metal layer by chemical vapor deposition.

14. The metallic stack recited in claim 13 wherein the ARC layer is deposited
on the metal layer by plasma enhanced chemical vapor deposition.

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15. The metallic stack recited in claim 9 wherein the stack is about 1,000 to
20,000 Angstrans thick.

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16. The metallic stack of claim 15 wherein the stack is about 5,000 to 8,000
Angstrans thick.

17. A semiconductor device, comprising:
an oxide layer formed on a wafer; and
at least one microelectronic structure extending from the oxide layer and
including:

5 a barrier layer disposed on the oxide layer;
a metal layer disposed on the barrier layer; and
an inorganic dielectric ARC layer disposed on the metal layer.

18. The semiconductor device recited in claim 17 wherein the at least one
10 microelectronic structure further includes a residual photoresist layer disposed on the
ARC layer.

19. The semiconductor device recited in claim 17 wherein the ARC layer
consists essentially of silicon oxynitride.

15 20. The semiconductor device recited in claim 19 wherein the ARC layer is
formed by plasma enhanced chemical vapor deposition.